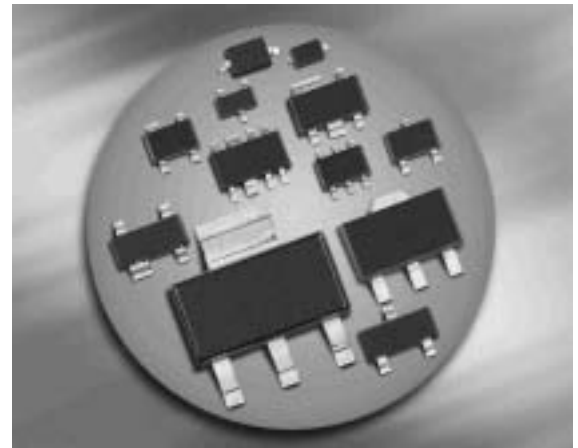
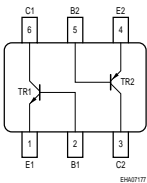


NPN/PNP Silicon AF Transistor Arrays

- For AF input stage and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Two (galvanic) internal isolated NPN/PNP transistor in one package
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101


BC846PN
BC846UPN
BC847PN


Type	Marking	Pin Configuration						Package
BC846PN	1Os	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BC846UPN	1Os	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SC74
BC847PN	1Ps	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

¹Pb-containing package may be available upon special request

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage BC846PN/UPN BC847PN	V_{CEO}	65 45	V
Collector-emitter voltage BC846PN/UPN BC847PN	V_{CES}	80 50	
Collector-base voltage BC846PN/UPN BC847PN	V_{CBO}	80 50	
Emitter-base voltage	V_{EBO}	6	
Collector current	I_C	100	mA
Peak collector current	I_{CM}	200	
Total power dissipation- $T_S \leq 115^\circ\text{C}$, BC846PN, BC847PN $T_S \leq 118^\circ\text{C}$, BC846UPN	P_{tot}	250 250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾ BC846PN, BC847PN BC846UPN	R_{thJS}	≤ 140 ≤ 130	K/W

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 10\text{ mA}$, $I_B = 0$, BC846PN/UPN $I_C = 10\text{ mA}$, $I_B = 0$, BC847PN	$V_{(BR)CEO}$	65 45	- -	- -	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$, BC846PN/UPN $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$, BC847PN	$V_{(BR)CBO}$	80 50	- -	- -	
Collector-emitter breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $V_{BE} = 0$, BC846PN/UPN $I_C = 10\text{ }\mu\text{A}$, $V_{BE} = 0$, BC847PN	$V_{(BR)CES}$	80 50	- -	- -	
Emitter-base breakdown voltage $I_E = 1\text{ }\mu\text{A}$, $I_C = 0$	$V_{(BR)EBO}$	6	-	-	
Collector-base cutoff current $V_{CB} = 50\text{ V}$, $I_E = 0$ $V_{CB} = 30\text{ V}$, $I_E = 0$, $T_A = 150\text{ }^\circ\text{C}$	I_{CBO}	- -	- -	0.015 5	μA
DC current gain- $I_C = 10\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$	h_{FE}	- 200	250 290	- 450	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{CEsat}	- -	90 200	300 650	mV
Base emitter saturation voltage- ¹⁾ $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{BEsat}	- -	700 900	- -	
Base-emitter voltage- ¹⁾ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$ $I_C = 10\text{ mA}$, $V_{CE} = 5\text{ V}$	$V_{BE(ON)}$	580 -	660 -	750 820	

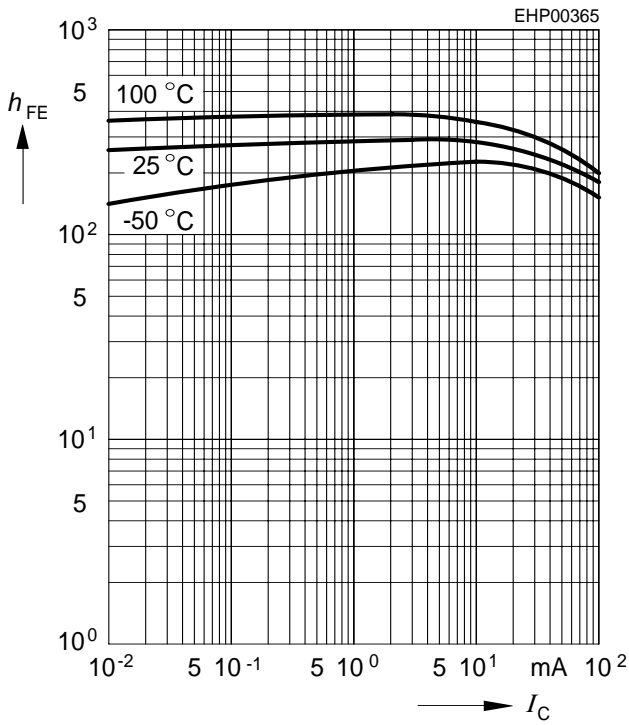
¹⁾Pulse test: $t = 300\mu\text{s}$, $D = 2\%$

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $I_C = 10\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 100\text{ MHz}$	f_T	-	250	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	1.5	-	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	8	-	
Short-circuit input impedance $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$	h_{11e}	-	4.5	-	k Ω
Open-circuit reverse voltage transf. ratio $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$	h_{12e}	-	2	-	10^{-4}
Short-circuit forward current transf. ratio $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$	h_{21e}	-	330	-	-
Open-circuit output admittance $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$	h_{22e}	-	30	-	μS

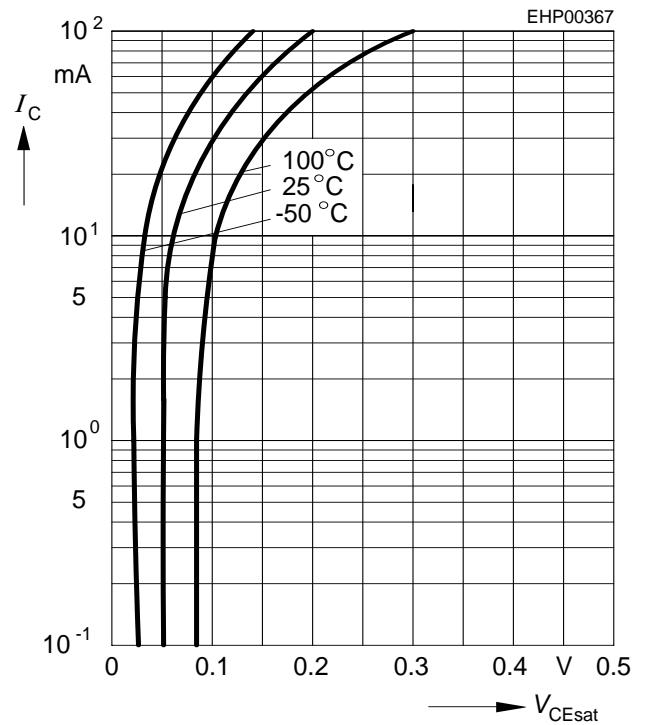
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5\text{ V}$



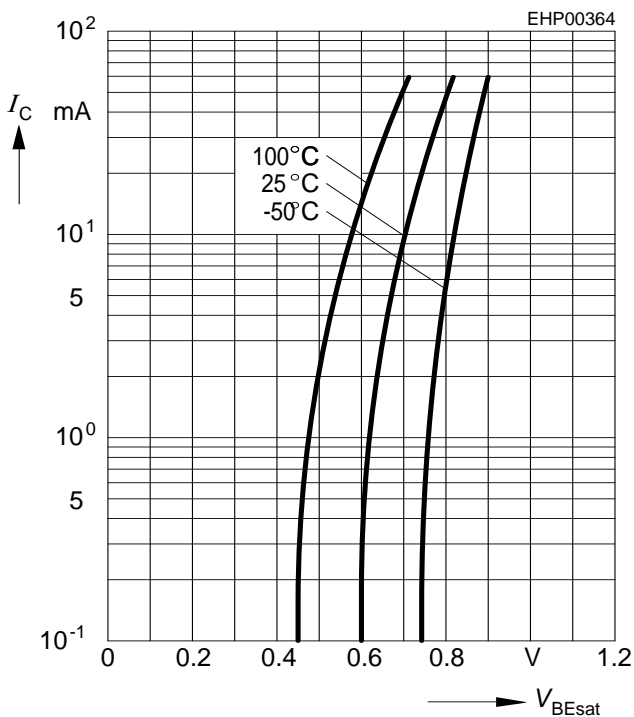
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 20$



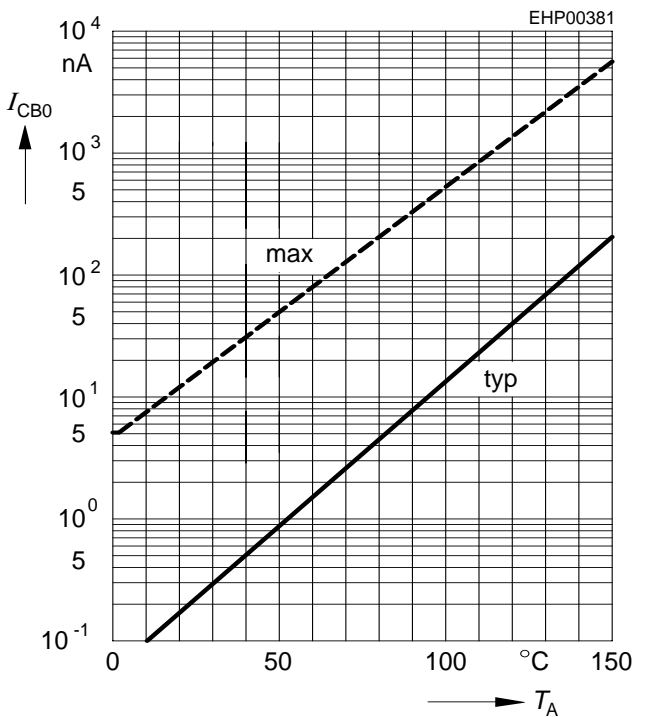
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 20$



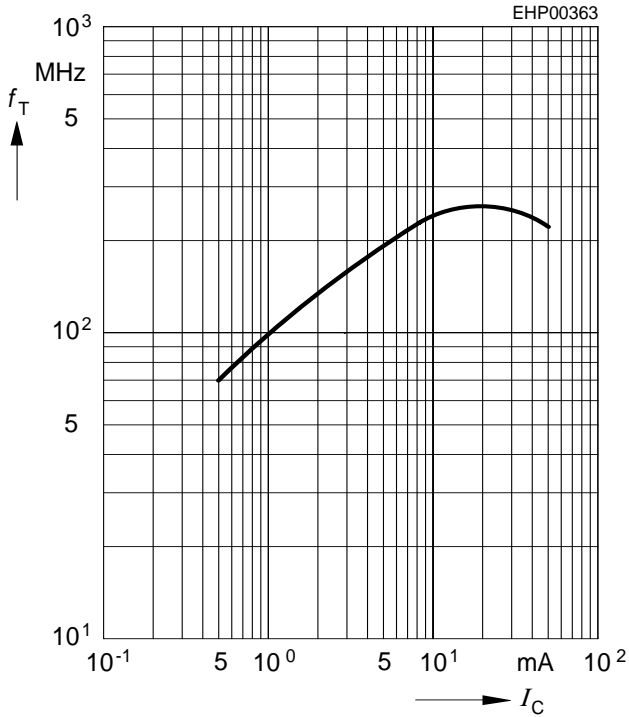
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CBO} = 30\text{ V}$



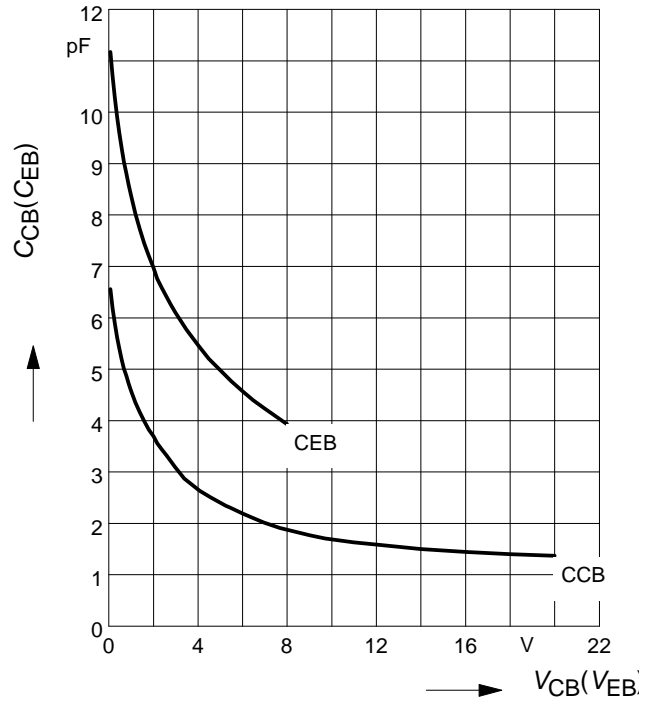
Transition frequency $f_T = f(I_C)$

$V_{CE} = 5\text{ V}, f = 100\text{ MHz}$



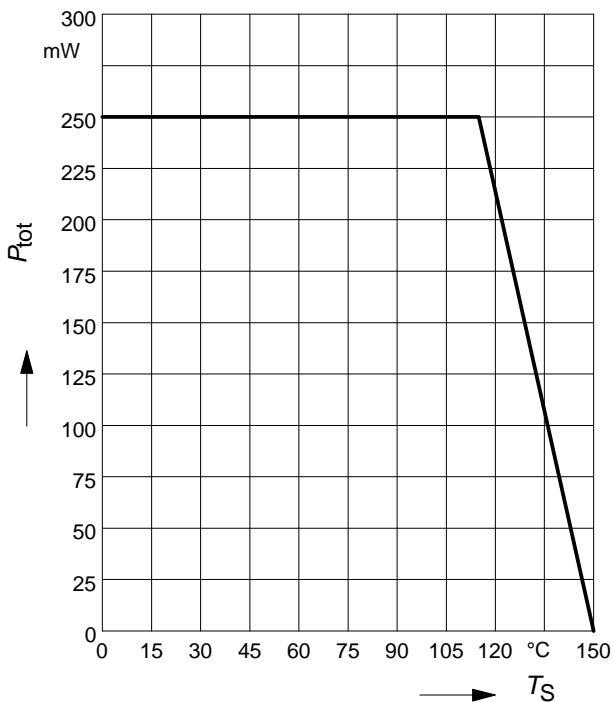
Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$



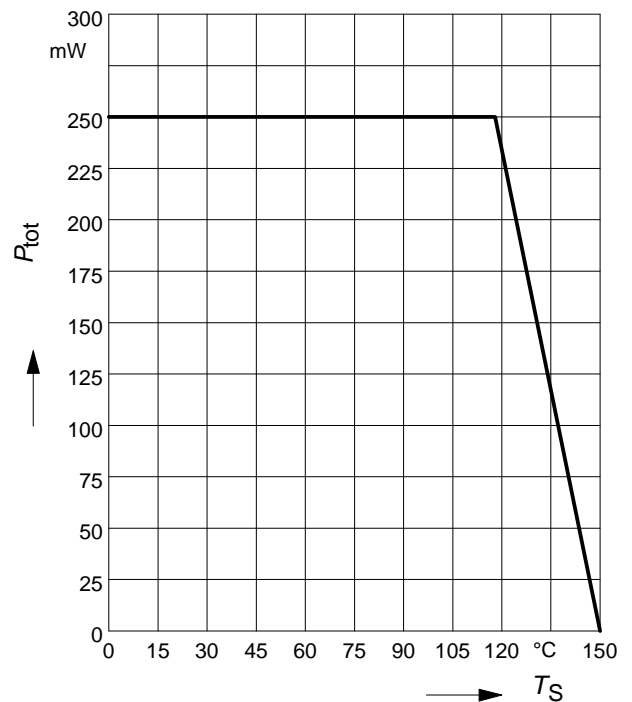
Total power dissipation $P_{tot} = f(T_S)$

BC846PN, BC847PN



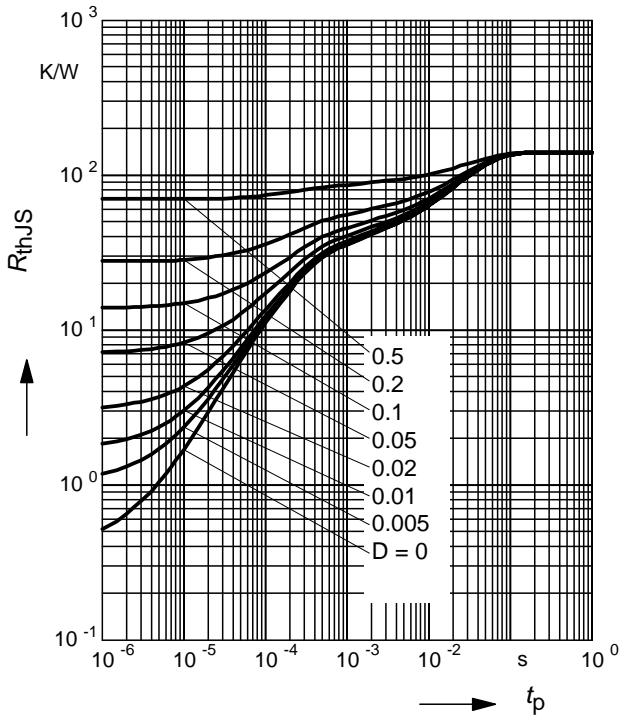
Total power dissipation $P_{tot} = f(T_S)$

BC846UPN



Permissible Pulse Load $R_{thJS} = f(t_p)$

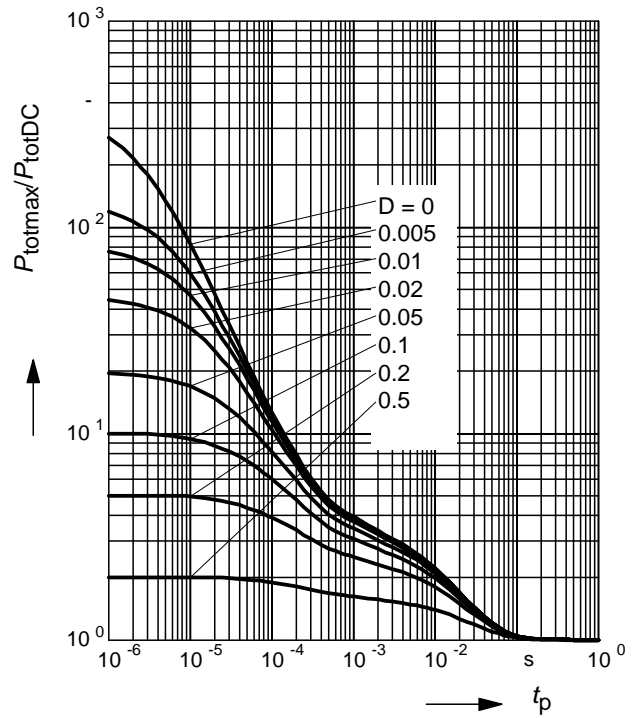
BC846PN, BC847PN



Permissible Pulse Load

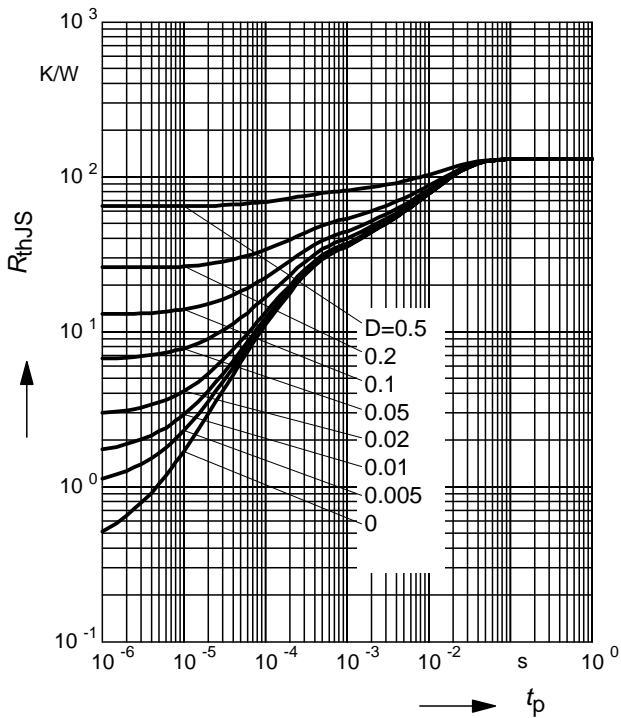
$P_{totmax}/P_{totDC} = f(t_p)$

BC846PN, BC847PN



Permissible Puls Load $R_{thJS} = f(t_p)$

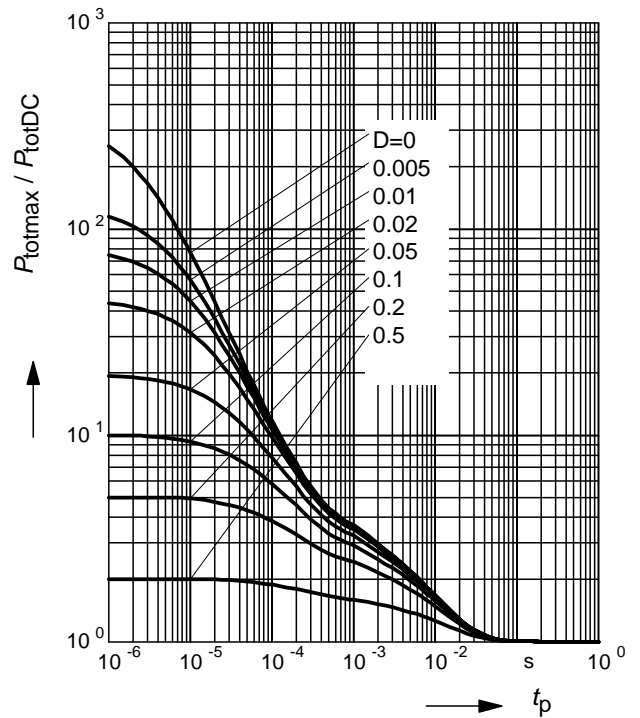
BC846UPN



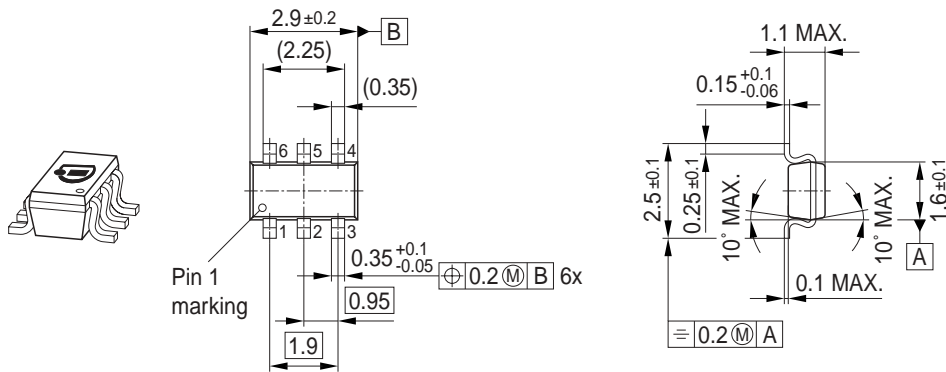
Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

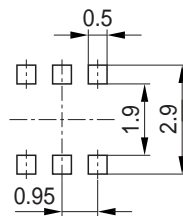
BC846UPN



Package Outline

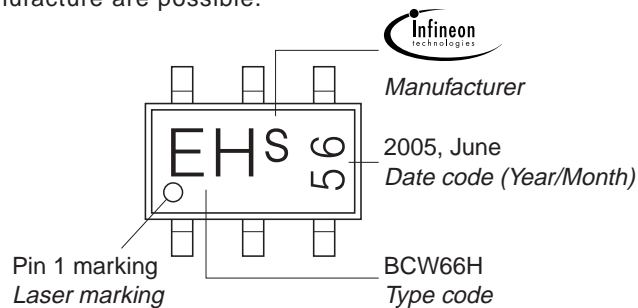


Foot Print



Marking Layout (Example)

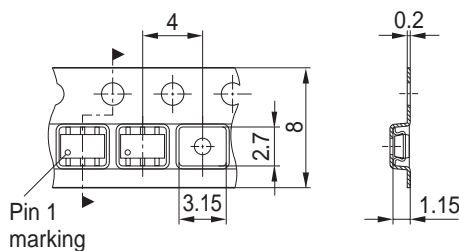
Small variations in positioning of Date code, Type code and Manufacture are possible.



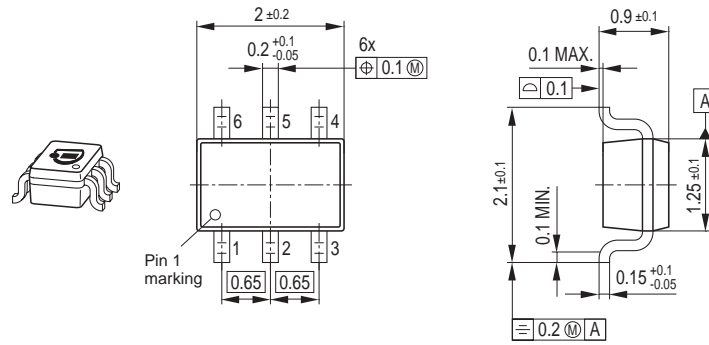
Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel

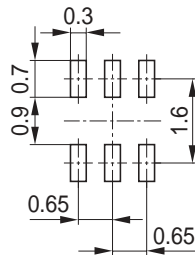
For symmetric types no defined Pin 1 orientation in reel.



Package Outline

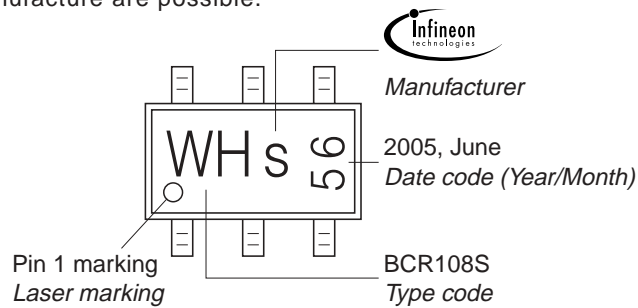


Foot Print



Marking Layout (Example)

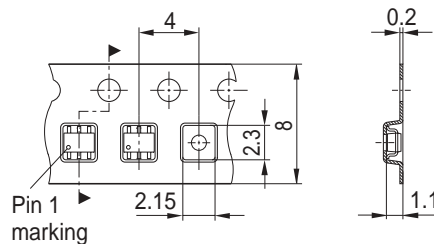
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



Edition 2006-02-01

Published by

Infineon Technologies AG

81726 München, Germany

© Infineon Technologies AG 2007.

All Rights Reserved.

Attention please!

The information given in this dokument shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie"). With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system.

Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.